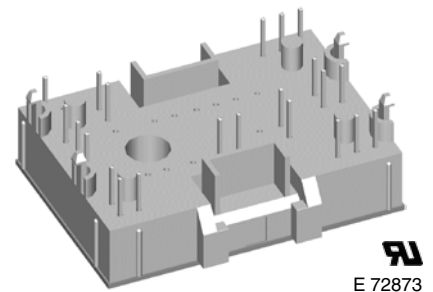
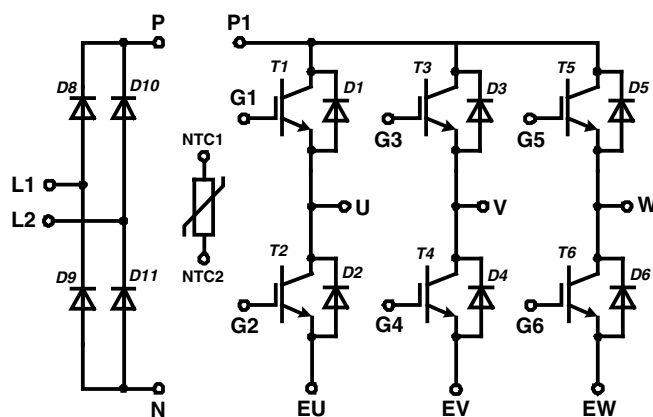


Converter - Brake - Inverter Module NPT IGBT

Single Phase Rectifier	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 600 \text{ V}$
$I_{DAVM25} = 35 \text{ A}$	$I_{C25} = 18 \text{ A}$
$I_{FSM} = 270 \text{ A}$	$V_{CE(sat)} = 2.1 \text{ V}$

Part name (Marking on product)

MIAA10WD600TMH



UL
E 72873

Pin configuration see outlines.

Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT IGBTs
 - low saturation voltage
 - positive temperature coefficient
 - fast switching
 - short tail current
- Epitaxial free wheeling diodes with hiperfast soft reverse recovery
- Temperature sense included

Application:

- AC motor drives
- Pumps, Fans
- Washing machines
- Air-conditioning system
- Inverter and power supplies

Package:

- "Mini" package
- Assembly height is 17 mm
- Insulated base plate
- Pins suitable for wave soldering and PCB mounting
- Assembly clips available
 - IXKU 5-505 screw clamp
 - IXRB 5-506 click clamp
- UL registered E72873

Output Inverter T1 - T6

				Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit	
V_{CES}	collector emitter voltage	$T_{VJ} = 150^{\circ}\text{C}$			600	V	
V_{GES}	max. DC gate voltage	continuous			± 20	V	
V_{GEM}	max. transient collector gate voltage	transient			± 30	V	
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			18	A	
I_{C80}		$T_C = 80^{\circ}\text{C}$			13	A	
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			70	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 10\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.1 2.3	2.6	V V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.35\text{ A}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	4.5	5.5	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.8	0.6	mA mA	
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			150	nA	
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		450		pF	
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 10\text{ A}$		50		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$	$T_{VJ} = 25^{\circ}\text{C}$	32		ns	
t_r	current rise time			35		ns	
$t_{d(off)}$	turn-off delay time			180		ns	
t_f	current fall time			110		ns	
E_{on}	turn-on energy per pulse			0.17		mJ	
E_{off}	turn-off energy per pulse			0.2		mJ	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$	32		ns	
t_r	current rise time			35		ns	
$t_{d(off)}$	turn-off delay time			190		ns	
t_f	current fall time			170		ns	
E_{on}	turn-on energy per pulse			0.27		mJ	
E_{off}	turn-off energy per pulse			0.42		mJ	
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega; I_C = 20\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$	$V_{CEK} \leq V_{CES} - L_S \cdot di/dt$		V	
I_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 360\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 82\ \Omega; t_p = 10\ \mu\text{s};$ non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$	40		A	
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.8	K/W	
R_{thCH}	thermal resistance case to heatsink			0.6		K/W	

Output Inverter D1 - D6

				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{RRM}	<i>max. repetitive reverse voltage</i>		$T_{VJ} = 150^{\circ}\text{C}$		600	V
I_{F25}	<i>forward current</i>		$T_C = 25^{\circ}\text{C}$		22	A
I_{F80}			$T_C = 80^{\circ}\text{C}$		14	A
V_F	<i>forward voltage</i>	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.7 1.4	2.2	V V
Q_{rr}	<i>reverse recovery charge</i>	$V_R = 300\text{ V}$ $di_F/dt = -300\text{ A}/\mu\text{s}$ $I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	0.3		μC
I_{RM}	<i>max. reverse recovery current</i>			8.8		A
t_{rr}	<i>reverse recovery time</i>			95		ns
E_{rec}	<i>reverse recovery energy</i>			22		μJ
R_{thJC}	<i>thermal resistance junction to case</i>	(per diode)			2.5	K/W
R_{thCH}	<i>thermal resistance case to heatsink</i>			0.85		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

IXYS reserves the right to change limits, test conditions and dimensions.

20070404a

Input Rectifier Bridge D8 - D11

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1600		V
I_{FAV}	average forward current	sine 180°	$T_C = 80^{\circ}\text{C}$		22		A
I_{DAVM}	max. average DC output current	rect.; $d = 1/2$	$T_C = 80^{\circ}\text{C}$		23		A
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}$; sine 50 Hz	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		270 tbd		A A
I^2t	I^2t value for fusing	$t = 10 \text{ ms}$; sine 50 Hz	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		365 tbd		A^2s A^2s
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$		50		W
V_F	forward voltage	$I_F = 30 \text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.35 1.35	1.6		V V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.3	0.01		mA mA
R_{thJC}	thermal resistance junction to case	(per diode)		0.7	2.1		K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)					K/W

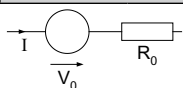
Temperature Sensor NTC

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
R_{25}	resistance	$T_C = 25^{\circ}\text{C}$	4.75	5.0	5.25		k Ω
$B_{25/50}$				3375			K

Module

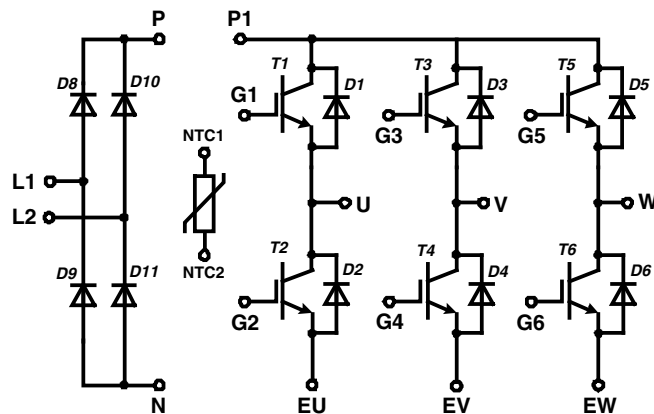
Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
T_{VJ}	operating temperature		-40		125		$^{\circ}\text{C}$
T_{VJM}	max. virtual junction temperature				150		$^{\circ}\text{C}$
T_{stg}	storage temperature		-40		125		$^{\circ}\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}$; 50/60 Hz			2500		V~
CTI	comparative tracking index				-		
F_C	mounting force		40		80		N
d_S	creep distance on surface		12.7				mm
d_A	strike distance through air		12				mm
Weight				35			g

Equivalent Circuits for Simulation



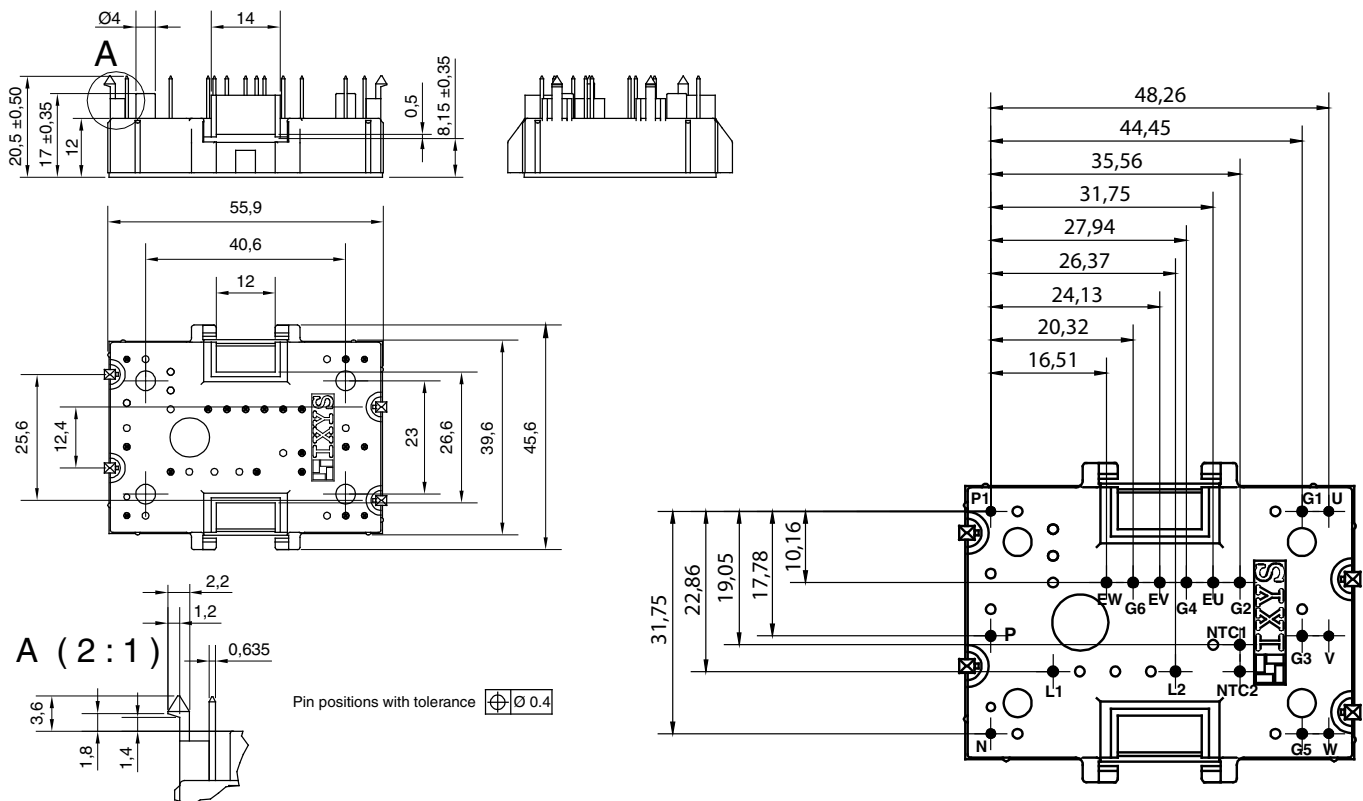
Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_0 R_0	rectifier diode	D8 - D11	$T_{VJ} = 125^{\circ}\text{C}$	0.9 16			V m Ω
V_0 R_0	IGBT	T1 - T6	$T_{VJ} = 125^{\circ}\text{C}$	1.0 125			V m Ω
V_0 R_0	free wheeling diode	D1 - D6	$T_{VJ} = 125^{\circ}\text{C}$	1.05 35			V m Ω

Circuit Diagram

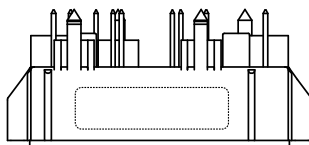


Outline Drawing

Dimensions in mm (1 mm = 0.0394")



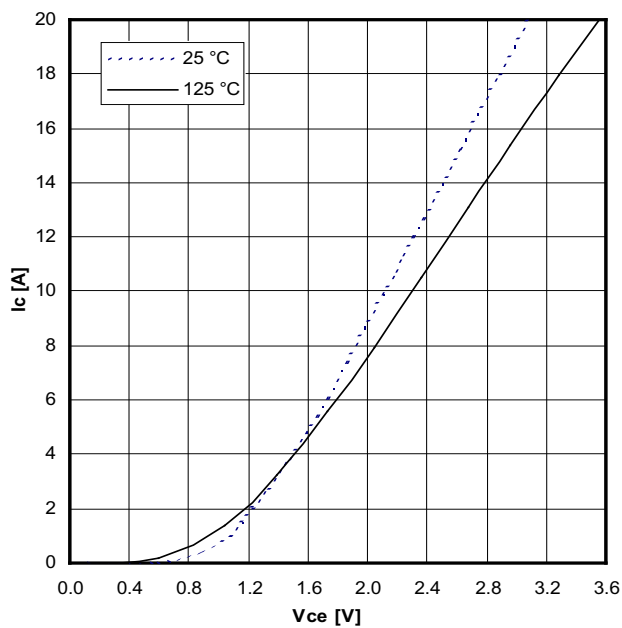
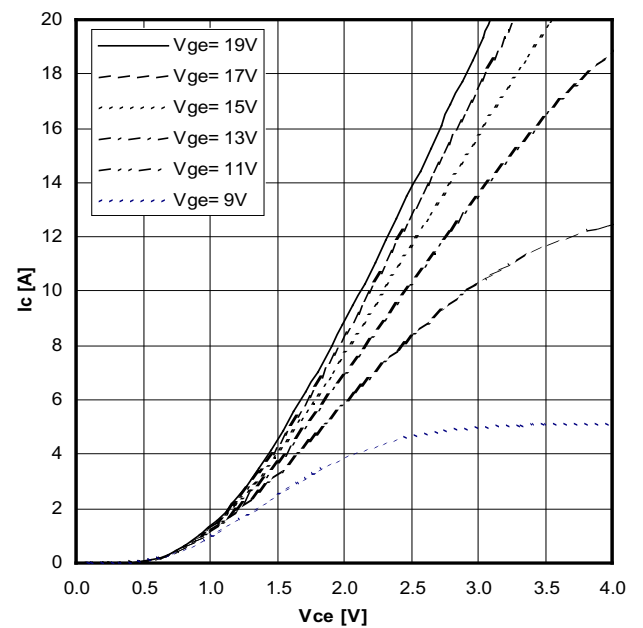
Product Marking



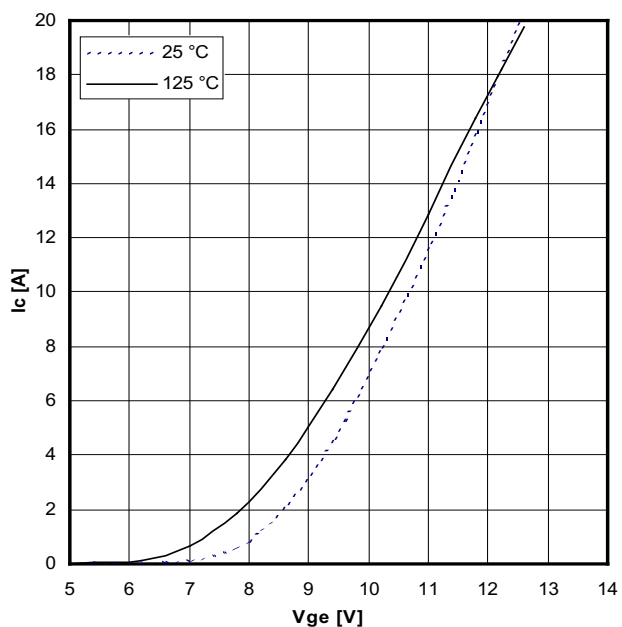
Part number

M = Module
 I = IGBT
 A = IGBT (NPT)
 A = Gen 1 / std
 10 = Current Rating [A]
 WD = 6-Pack + 1~ Rectifier Bridge
 600 = Reverse Voltage [V]
 T = NTC
 MH = MiniPack2

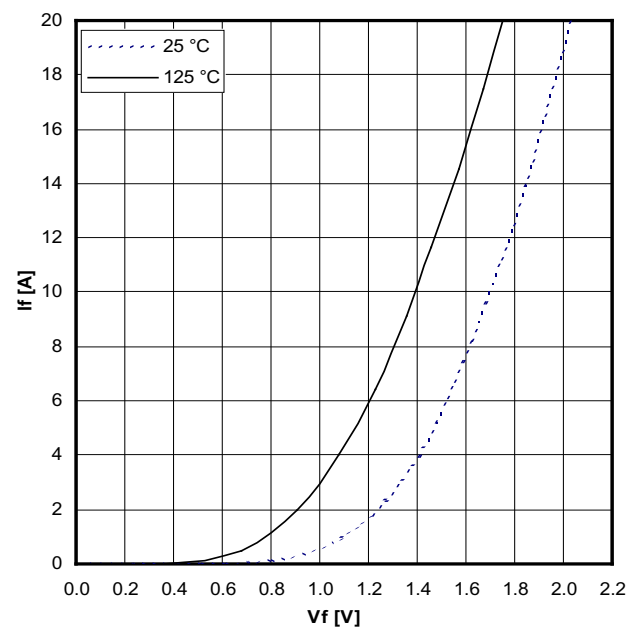
Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MIAA 10 WD 600 TMH	MIAA10WD600TMH	Box	20	502221


Typical output characteristics, $V_{GE} = 15\text{ V}$


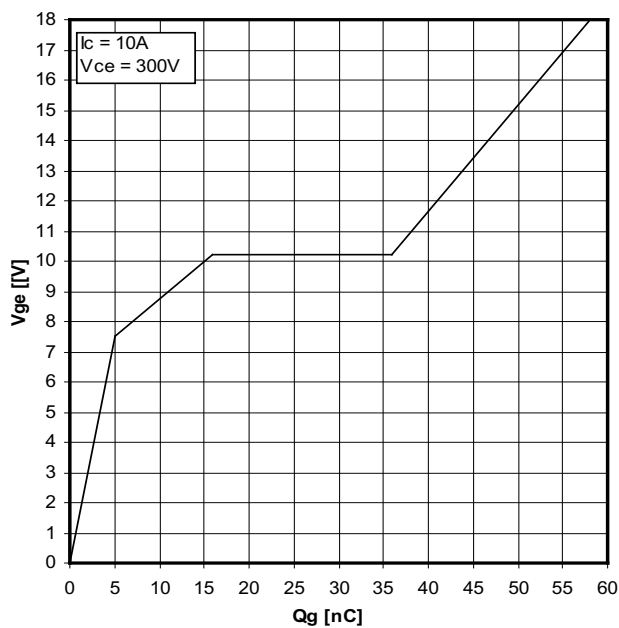
Typical output characteristics (125 °C)



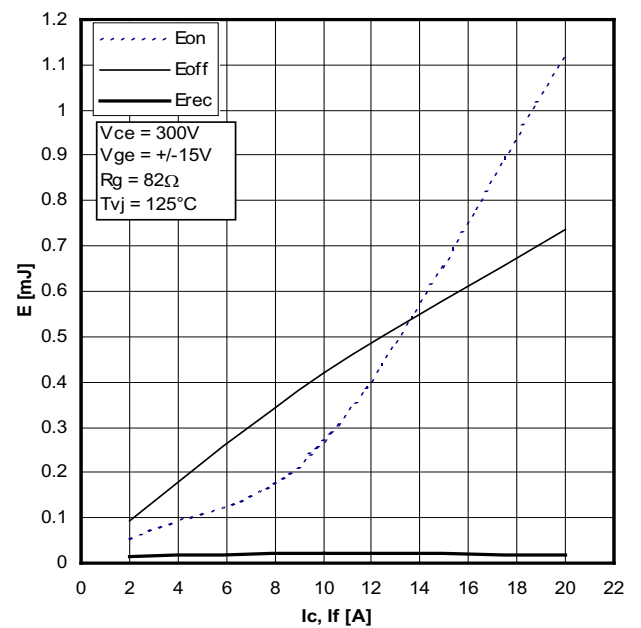
Typical transfer characteristics



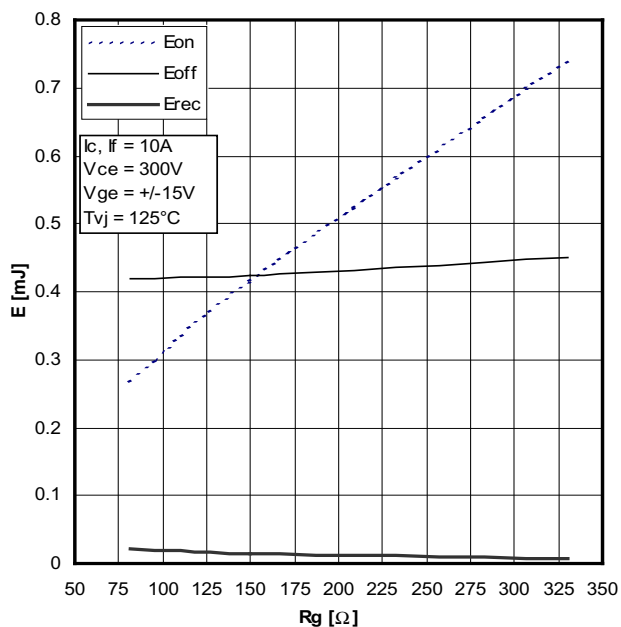
Typical forward characteristics of freewheeling diode



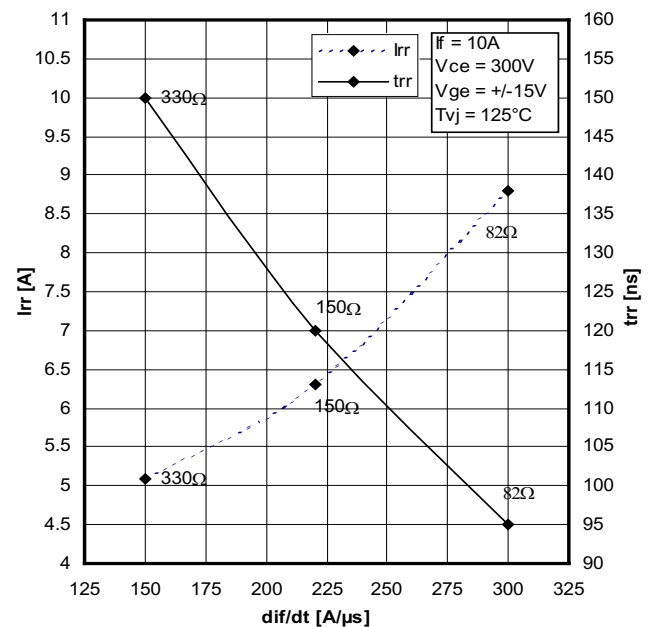
Typical turn on gate charge



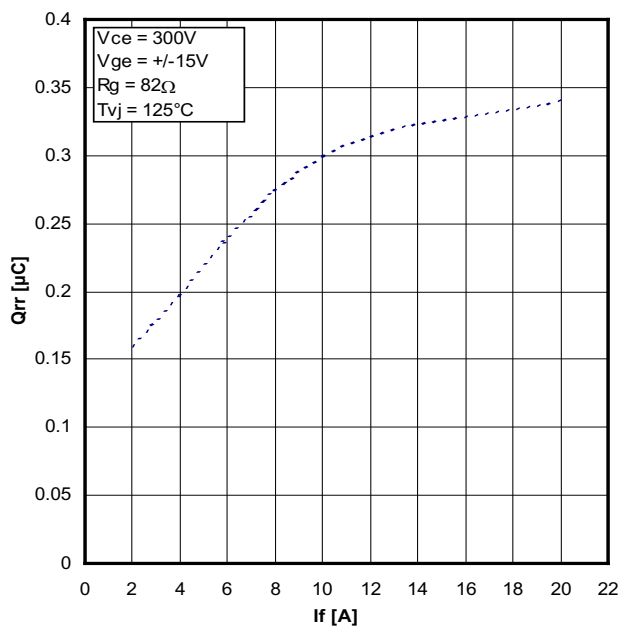
Typical switching energy versus collector current



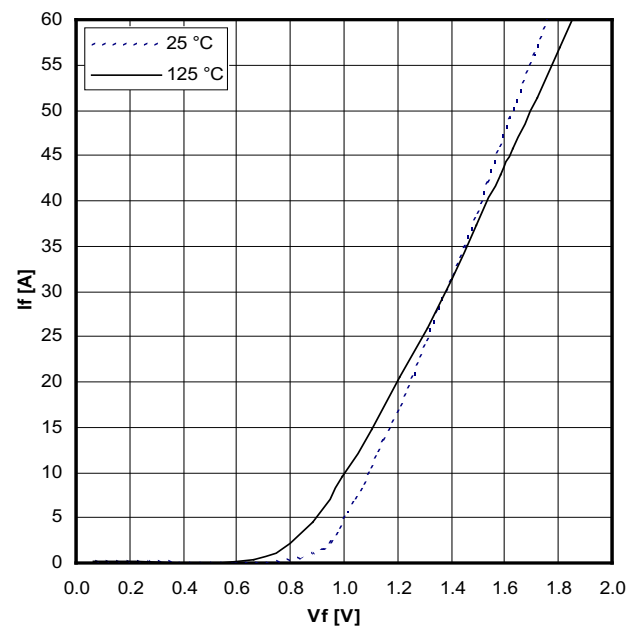
Typical switching energy versus gate resistance



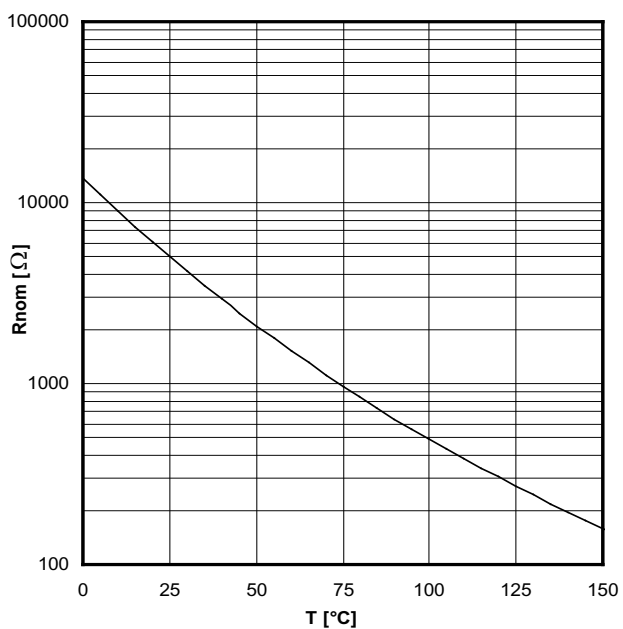
Typical turn-off characteristics of free wheeling diode



Typical turn-off characteristics of free wheeling diode



Typical forward characteristics per rectifier



Typical thermistor resistance versus temperature